

74LV14

Hex inverting Schmitt trigger

Rev. 03 — 20 December 2007

Product data sheet

1. General description

The 74LV14 is a low-voltage Si-gate CMOS device that is pin and function compatible with 74HC14 and 74HCT14.

The 74LV14 provides six inverting buffers with Schmitt-trigger input. It is capable of transforming slowly-changing input signals into sharply defined, jitter-free output signals.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H .

2. Features

- Wide operating voltage: 1.0 V to 5.5 V
- Optimized for low voltage applications: 1.0 V to 3.6 V
- Accepts TTL input levels between $V_{CC} = 2.7$ V and $V_{CC} = 3.6$ V
- Typical output ground bounce < 0.8 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- Typical HIGH-level output voltage (V_{OH}) undershoot: > 2 V at $V_{CC} = 3.3$ V and $T_{amb} = 25$ °C
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to $+85$ °C and from -40 °C to $+125$ °C

3. Applications

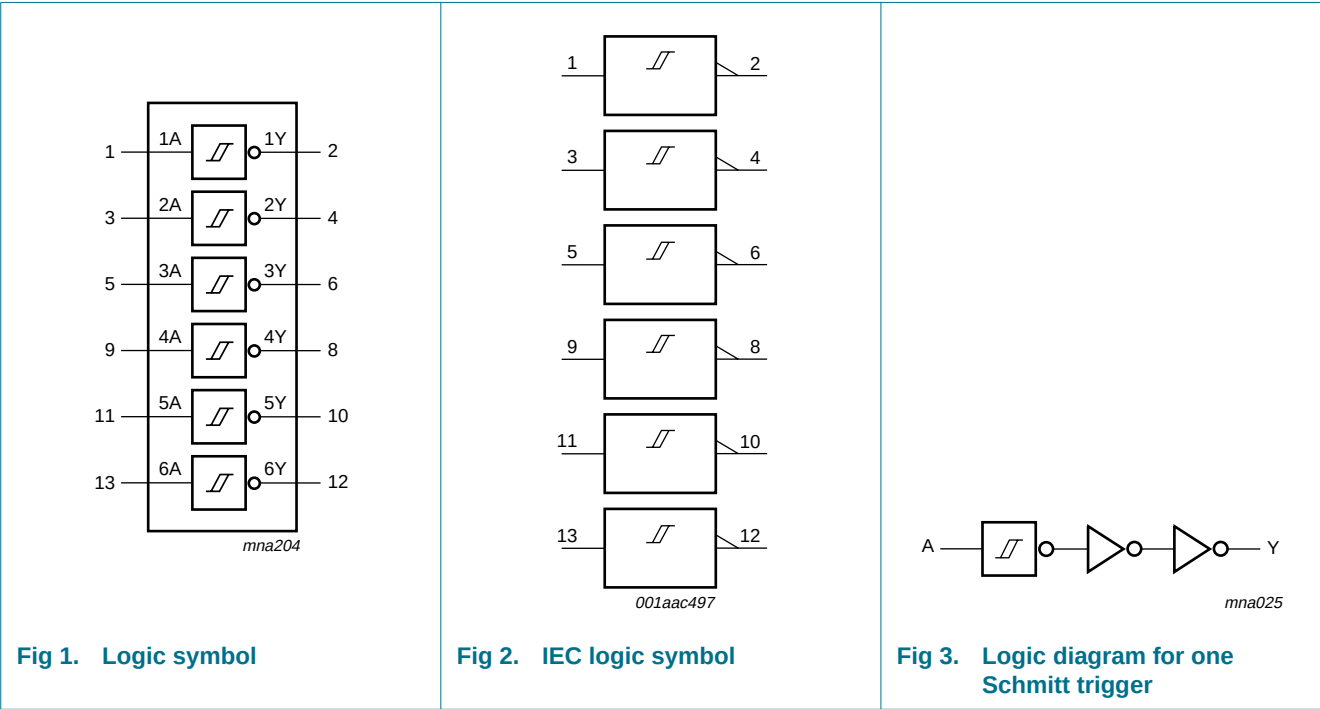
- Wave and pulse shapers for highly noisy environments
- Astable multivibrators
- Monostable multivibrators

4. Ordering information

Table 1. Ordering information

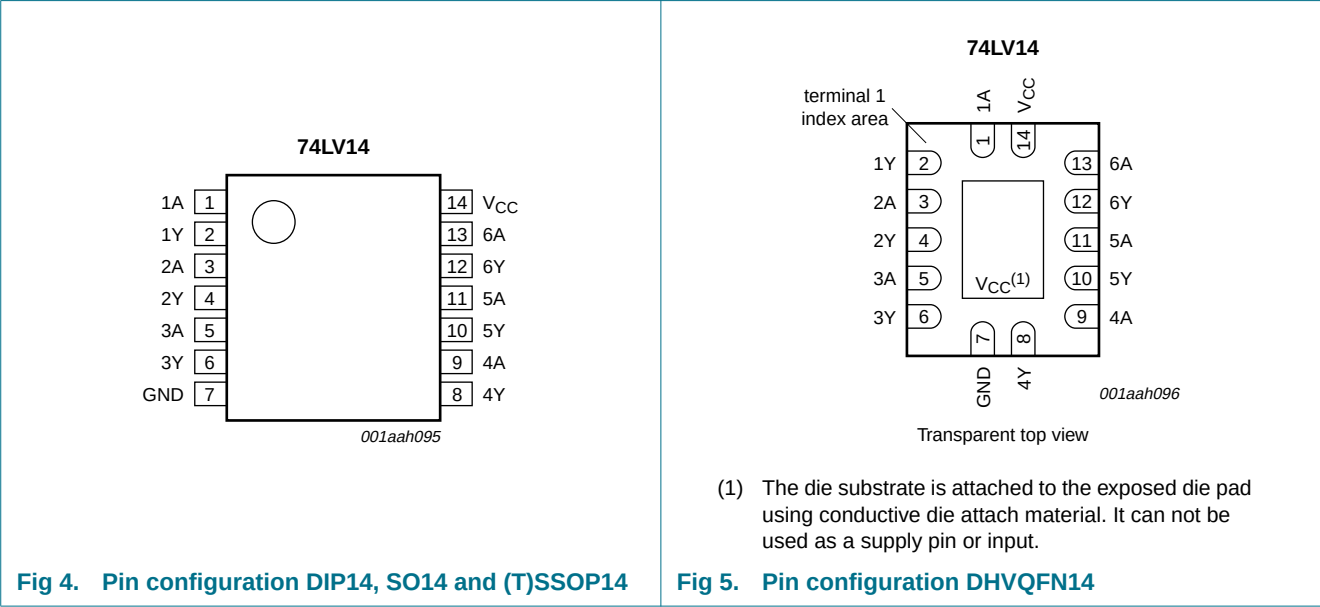
Type number	Package			
	Temperature range	Name	Description	Version
74LV14N	−40 °C to +125 °C	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
74LV14D	−40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74LV14DB	−40 °C to +125 °C	SSOP14	plastic shrink small outline package; 14 leads; body width 5.3 mm	SOT337-1
74LV14PW	−40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74LV14BQ	−40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 × 3 × 0.85 mm	SOT762-1

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	data input
1Y	2	data output
2A	3	data input
2Y	4	data output
3A	5	data input
3Y	6	data output
GND	7	ground (0 V)
4Y	8	data output
4A	9	data input
5Y	10	data output
5A	11	data input
6Y	12	data output
6A	13	data input
V _{CC}	14	supply voltage

7. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level.

Input nA	Output nY
L	H
H	L

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	± 50	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	-	± 25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$			
	DIP14 package		[2] -	750	mW
	SO14 package		[3] -	500	mW
	(T)SSOP14 package		[4] -	500	mW
	DHVQFN14 package		[5] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] P_{tot} derates linearly with 12 mW/K above 70 °C.

[3] P_{tot} derates linearly with 8 mW/K above 70 °C.

[4] P_{tot} derates linearly with 5.5 mW/K above 60 °C.

[5] P_{tot} derates linearly with 4.5 mW/K above 60 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CC}	supply voltage	[1]	1.0	3.3	5.5	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		−40	+25	+125	°C

[1] The static characteristics are guaranteed from $V_{CC} = 1.2\text{ V}$ to $V_{CC} = 5.5\text{ V}$, but LV devices are guaranteed to function down to $V_{CC} = 1.0\text{ V}$ (with input levels GND or V_{CC}).

10. Static characteristics

Table 6. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = –100 µA; V _{CC} = 1.2 V	-	1.2	-	-	-	V
		I _O = –100 µA; V _{CC} = 2.0 V	1.8	2.0	-	1.8	-	V
		I _O = –100 µA; V _{CC} = 2.7 V	2.5	2.7	-	2.5	-	V
		I _O = –100 µA; V _{CC} = 3.0 V	2.8	3.0	-	2.8	-	V
		I _O = –100 µA; V _{CC} = 4.5 V	4.3	4.5	-	4.3	-	V
		I _O = –6 mA; V _{CC} = 3.0 V	2.4	2.82	-	2.2	-	V
		I _O = –12 mA; V _{CC} = 4.5 V	3.6	4.2	-	3.5	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 100 µA; V _{CC} = 1.2 V	-	0	-	-	-	V
		I _O = 100 µA; V _{CC} = 2.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 2.7 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 3.0 V	-	0	0.2	-	0.2	V
		I _O = 100 µA; V _{CC} = 4.5 V	-	0	0.2	-	0.2	V
		I _O = 6 mA; V _{CC} = 3.0 V	-	0.25	0.40	-	0.50	V
		I _O = 12 mA; V _{CC} = 4.5 V	-	0.35	0.55	-	0.65	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	-	1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	20.0	-	40	µA
ΔI _{CC}	additional supply current	per input; V _I = V _{CC} – 0.6 V; V _{CC} = 2.7 V to 3.6 V	-	-	500	-	850	µA
C _I	input capacitance		-	3.5	-	-	-	pF

[1] Typical values are measured at T_{amb} = 25 °C.

11. Dynamic characteristics

Table 7. Dynamic characteristics
GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
t_{pd}	propagation delay	nA, to nY; see Figure 6 ^[2]						
		$V_{CC} = 1.2\text{ V}$	-	80	-	-	-	ns
		$V_{CC} = 2.0\text{ V}$	-	27	37	-	48	ns
		$V_{CC} = 2.7\text{ V}$	-	20	28	-	35	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}; C_L = 15\text{ pF}$ ^[3]	-	13	-	-	-	ns
		$V_{CC} = 3.0\text{ V to }3.6\text{ V}$ ^[3]	-	15	22	-	28	ns
		$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	-	18	-	23	ns
C_{PD}	power dissipation capacitance	$C_L = 50\text{ pF}; f_i = 1\text{ MHz}; V_i = \text{GND to }V_{CC}$ ^[4]	-	15	-	-	-	pF

[1] All typical values are measured at $T_{amb} = 25\text{ °C}$.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3\text{ V}$).

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz, f_o = output frequency in MHz

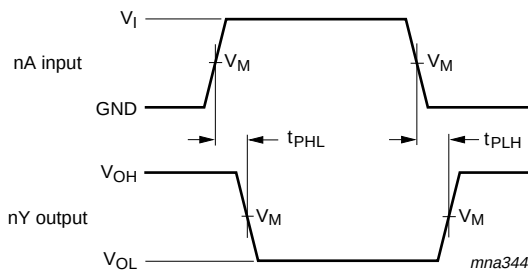
C_L = output load capacitance in pF

V_{CC} = supply voltage in V

N = number of inputs switching

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



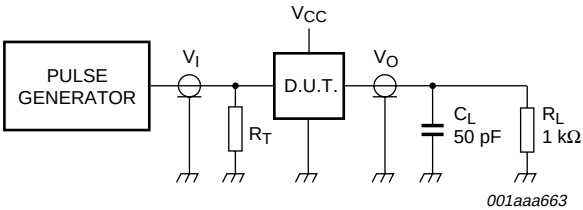
Measurement points are given in Table 8.

V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 6. The input (nA) to output (nY) propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
< 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V to 3.6 V	1.5 V	1.5 V
≥ 4.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in [Table 9](#).
 Definitions test circuit:
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.

Fig 7. Load circuit for switching times

Table 9. Test data

Supply voltage	Input	
V_{CC}	V_I	t_r, t_f
< 2.7 V	V_{CC}	≤ 2.5 ns
2.7 V to 3.6 V	2.7 V	≤ 2.5 ns
≥ 4.5 V	V_{CC}	≤ 2.5 ns

13. Transfer characteristics

Table 10. Transfer characteristics
GND = 0 V; For test circuit see [Figure 7](#).

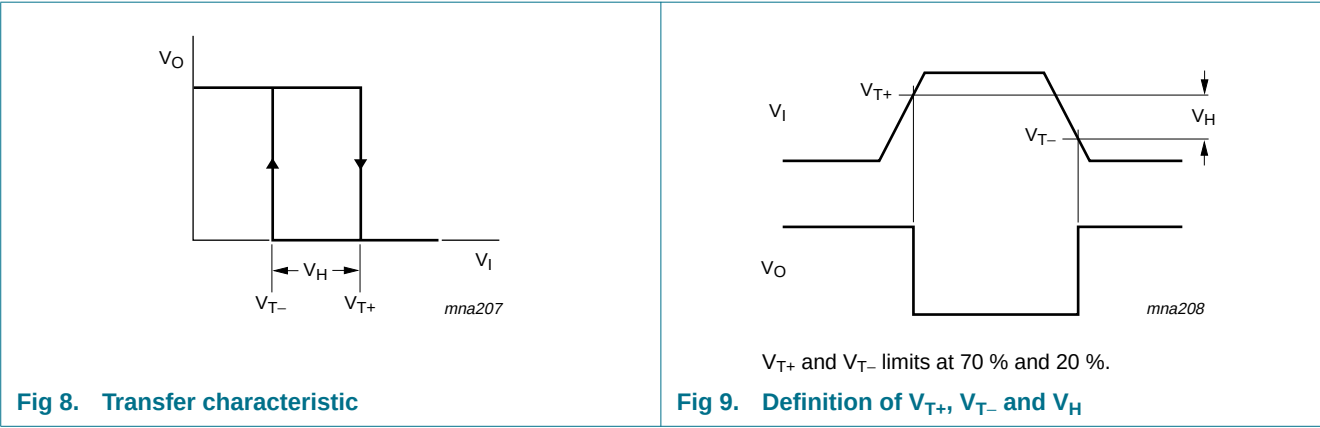
Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V_{T+}	positive-going threshold voltage	see Figure 6						
		$V_{CC} = 1.2\text{ V}$	-	0.70	-	-	-	V
		$V_{CC} = 2.0\text{ V}$	0.8	1.10	1.4	0.8	1.4	V
		$V_{CC} = 2.7\text{ V}$	1.0	1.45	2.0	1.0	2.0	V
		$V_{CC} = 3.0\text{ V}$	1.2	1.60	2.2	1.2	2.2	V
		$V_{CC} = 3.6\text{ V}$	1.5	1.95	2.4	1.5	2.4	V
		$V_{CC} = 4.5\text{ V}$	1.7	2.50	3.15	1.7	3.15	V
		$V_{CC} = 5.5\text{ V}$	2.1	3.00	3.85	2.1	3.85	V

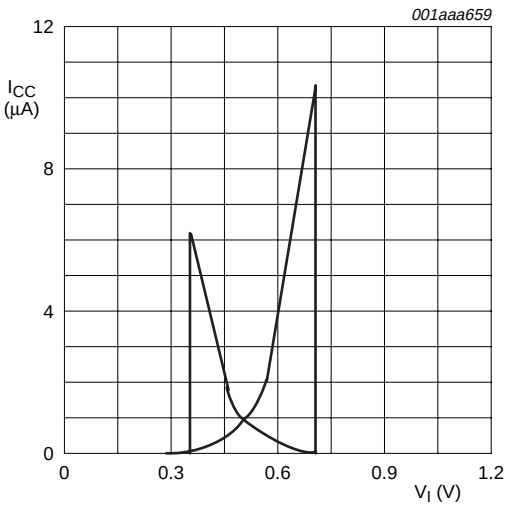
Table 10. Transfer characteristics ...continued
GND = 0 V; For test circuit see Figure 7.

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
V _{T−}	negative-going threshold voltage	see Figure 6						
		V _{CC} = 1.2 V	-	0.34	-	-	-	V
		V _{CC} = 2.0 V	0.3	0.65	0.9	0.3	0.9	V
		V _{CC} = 2.7 V	0.4	0.90	1.4	0.4	1.4	V
		V _{CC} = 3.0 V	0.6	1.05	1.5	0.6	1.5	V
		V _{CC} = 3.6 V	0.8	1.30	1.8	0.8	1.8	V
		V _{CC} = 4.5 V	0.9	1.60	2.0	0.9	2.0	V
V _H	hysteresis voltage (V _{T+} − V _{T−}); see Figure 6	V _{CC} = 1.2 V	-	0.3	-	-	-	V
		V _{CC} = 2.0 V	0.2	0.55	0.8	0.2	0.8	V
		V _{CC} = 2.7 V	0.3	0.60	1.1	0.3	1.1	V
		V _{CC} = 3.0 V	0.4	0.65	1.2	0.4	1.2	V
		V _{CC} = 3.6 V	0.4	0.70	1.2	0.4	1.2	V
		V _{CC} = 4.5 V	0.4	0.80	1.4	0.4	1.4	V
		V _{CC} = 5.5 V	0.6	1.00	1.5	0.6	1.5	V

[1] All typical values are measured at T_{amb} = 25 °C.

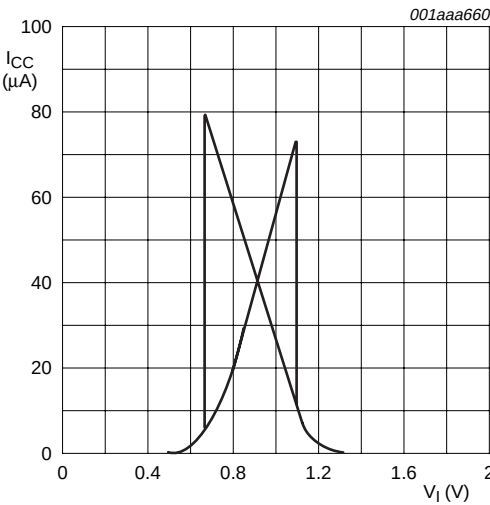
14. Waveforms transfer characteristics





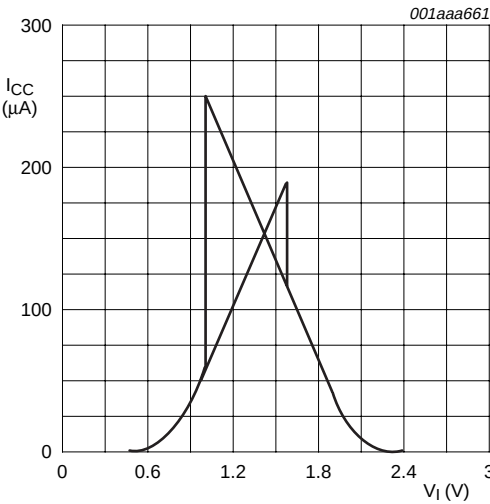
$V_{CC} = 1.2\text{ V}$.

Fig 10. Typical 74LV14 transfer characteristics



$V_{CC} = 2.0\text{ V}$.

Fig 11. Typical 74LV14 transfer characteristics



$V_{CC} = 3.0\text{ V}$.

Fig 12. Typical 74LV14 transfer characteristics

15. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

$$P_{\text{add}} = f_i \times (t_r \times \Delta I_{\text{CC(AV)}} + t_f \times \Delta I_{\text{CC(AV)}}) \times V_{\text{CC}} \text{ where:}$$

P_{add} = additional power dissipation (μW);

f_i = input frequency (MHz);

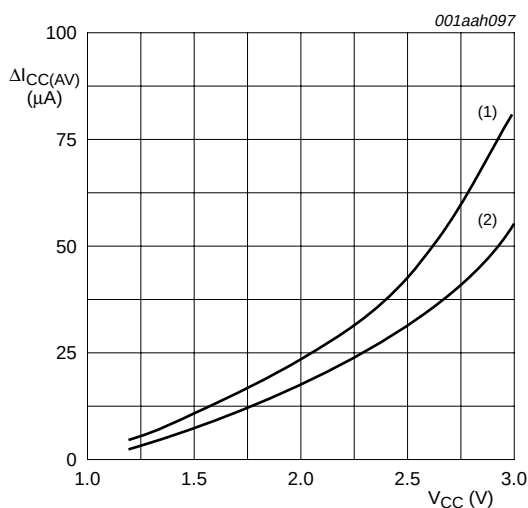
t_r = rise time (ns); 10 % to 90 %;

t_f = fall time (ns); 90 % to 10 %;

$\Delta I_{\text{CC(AV)}}$ = average additional supply current (μA).

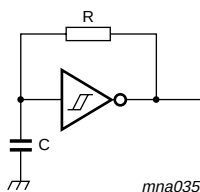
Average $\Delta I_{\text{CC(AV)}}$ differs with positive or negative input transitions, as shown in [Figure 13](#).

An example of a relaxation circuit using the 74LV14 is shown in [Figure 14](#).



- (1) Positive-going edge.
- (2) Negative-going edge.

Fig 13. Average additional supply current as a function of V_{CC}



$$f = \frac{1}{T} \approx \frac{1}{0.8 \times RC}$$

Fig 14. Relaxation oscillator

16. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1

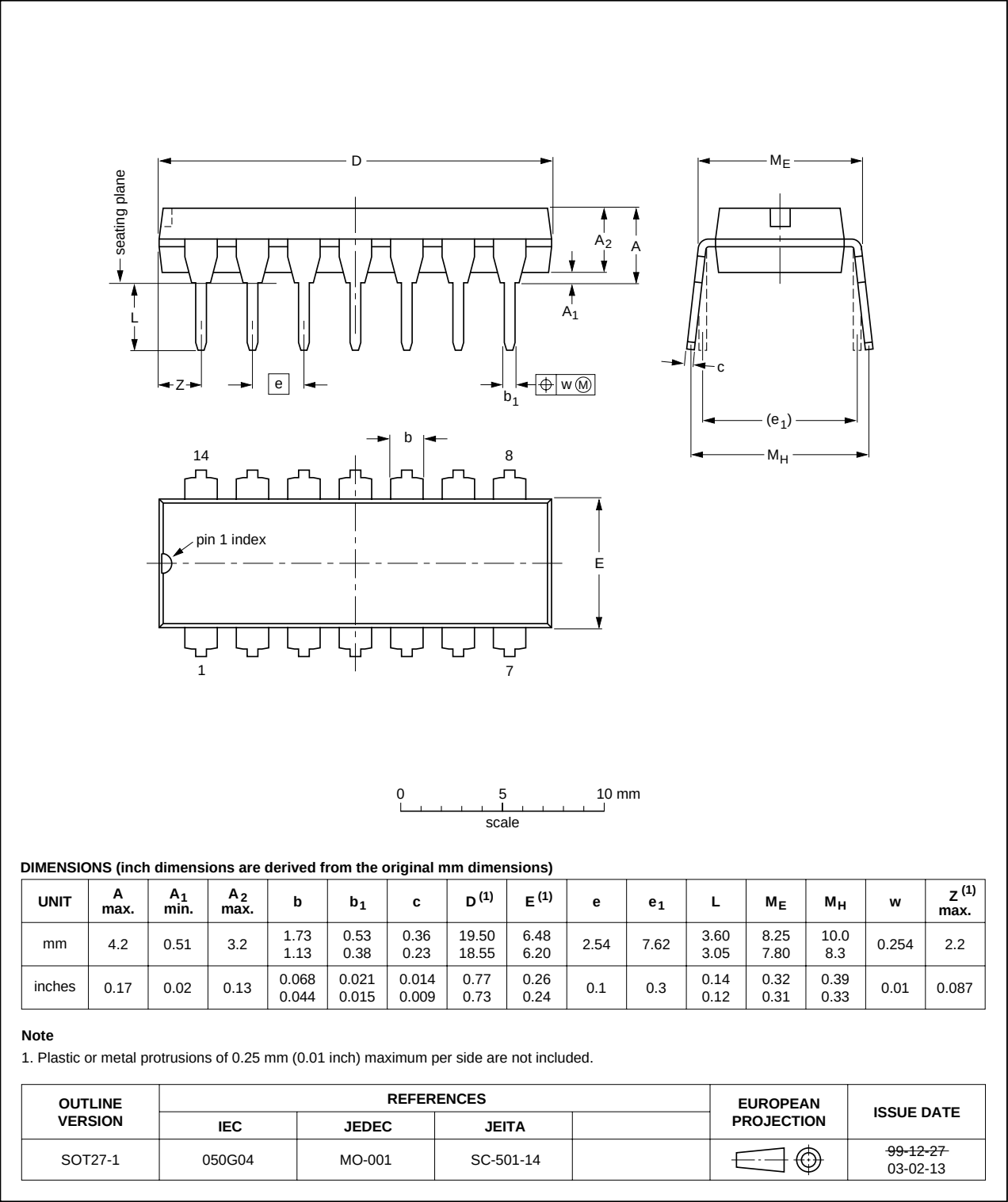


Fig 15. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

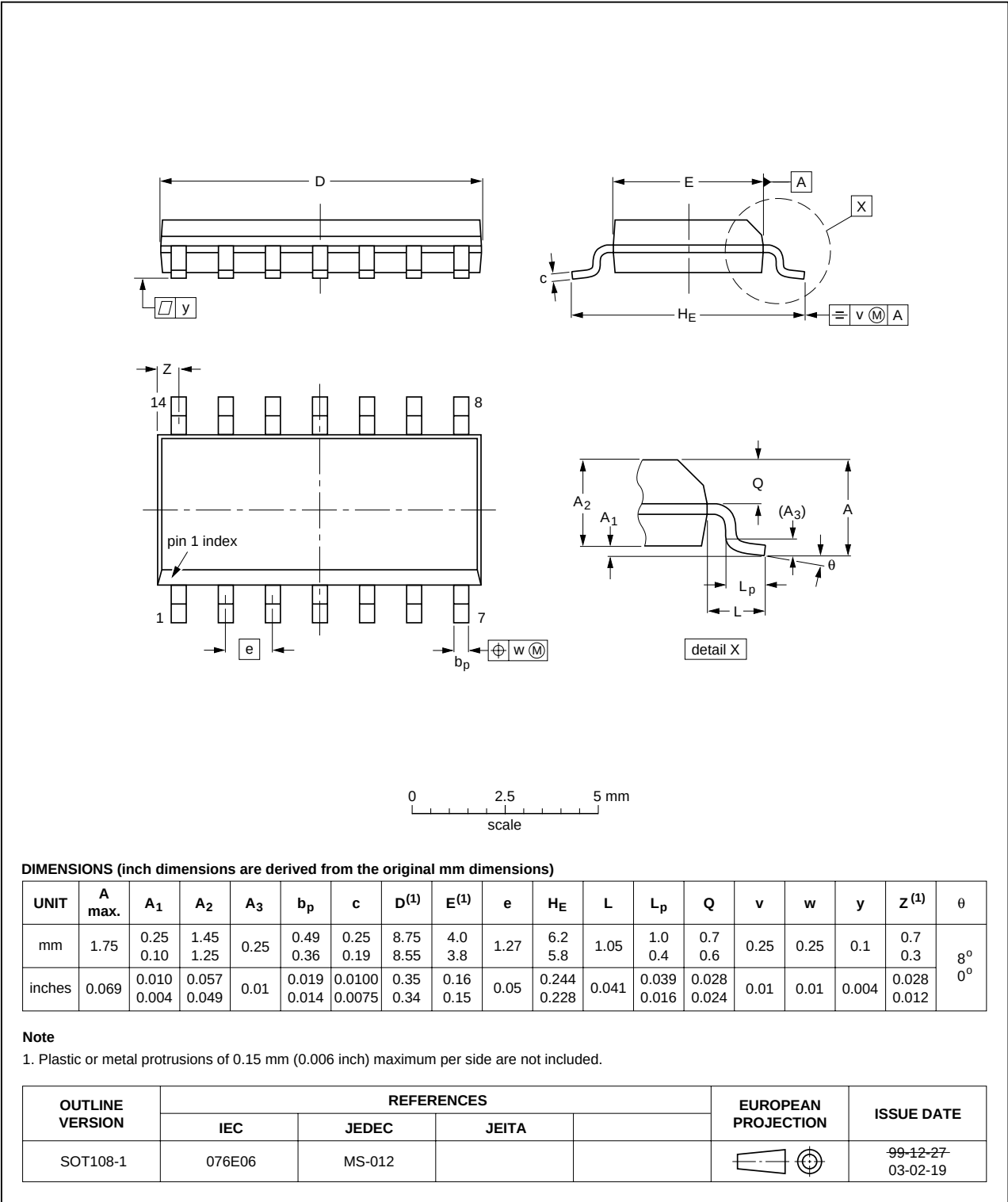


Fig 16. Package outline SOT108-1 (SO14)

SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1

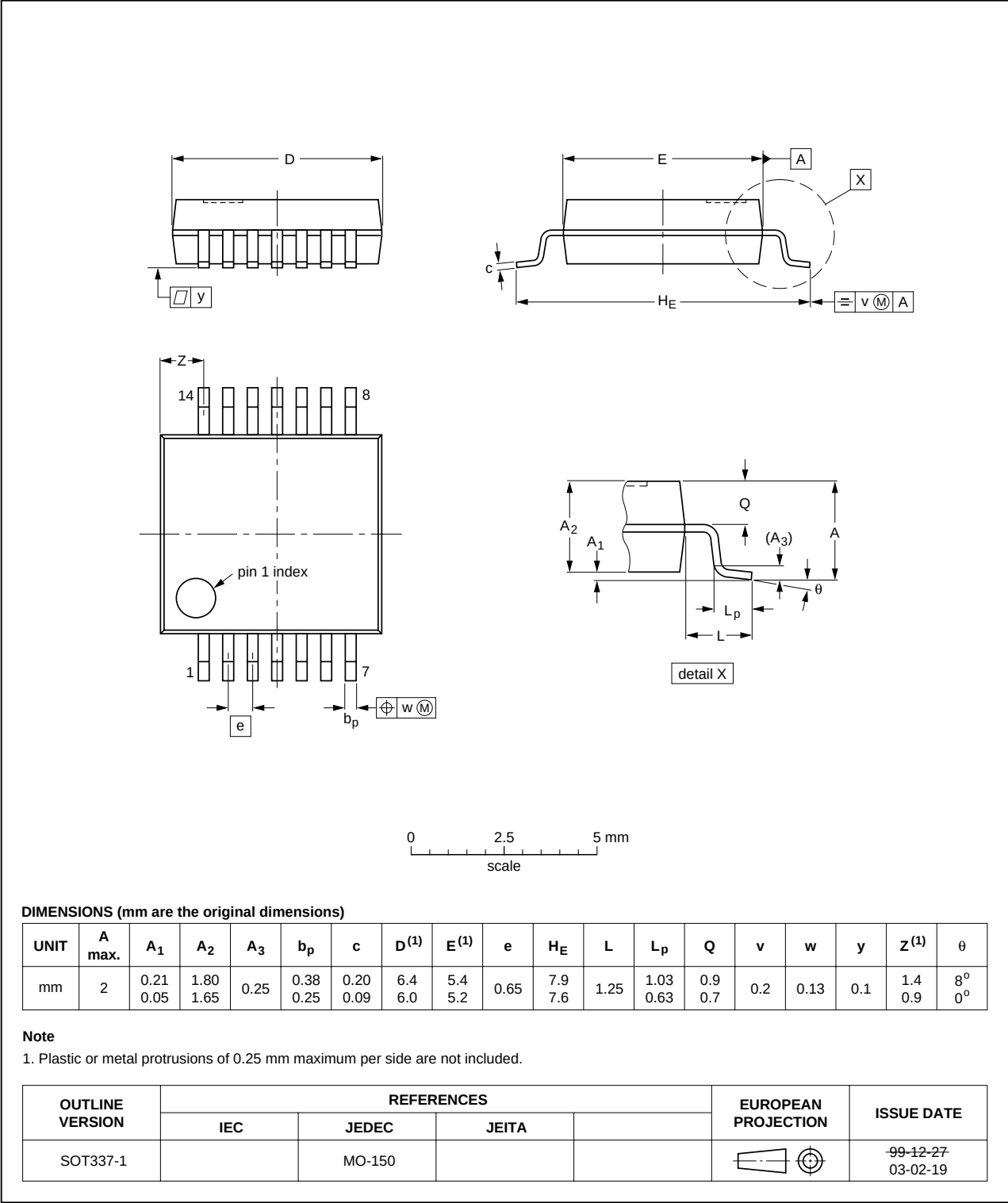


Fig 17. Package outline SOT337-1 (SSOP14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

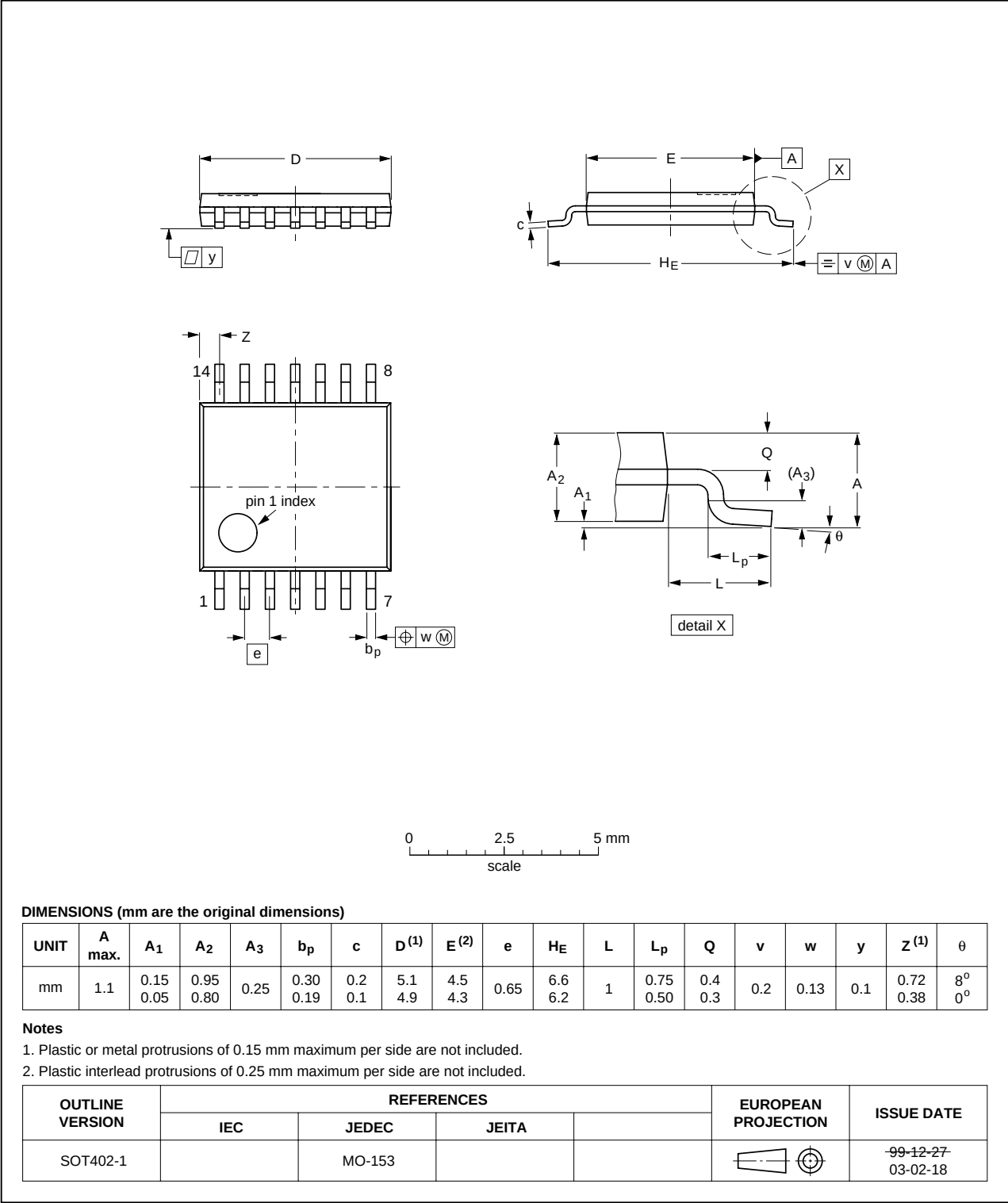


Fig 18. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm
SOT762-1

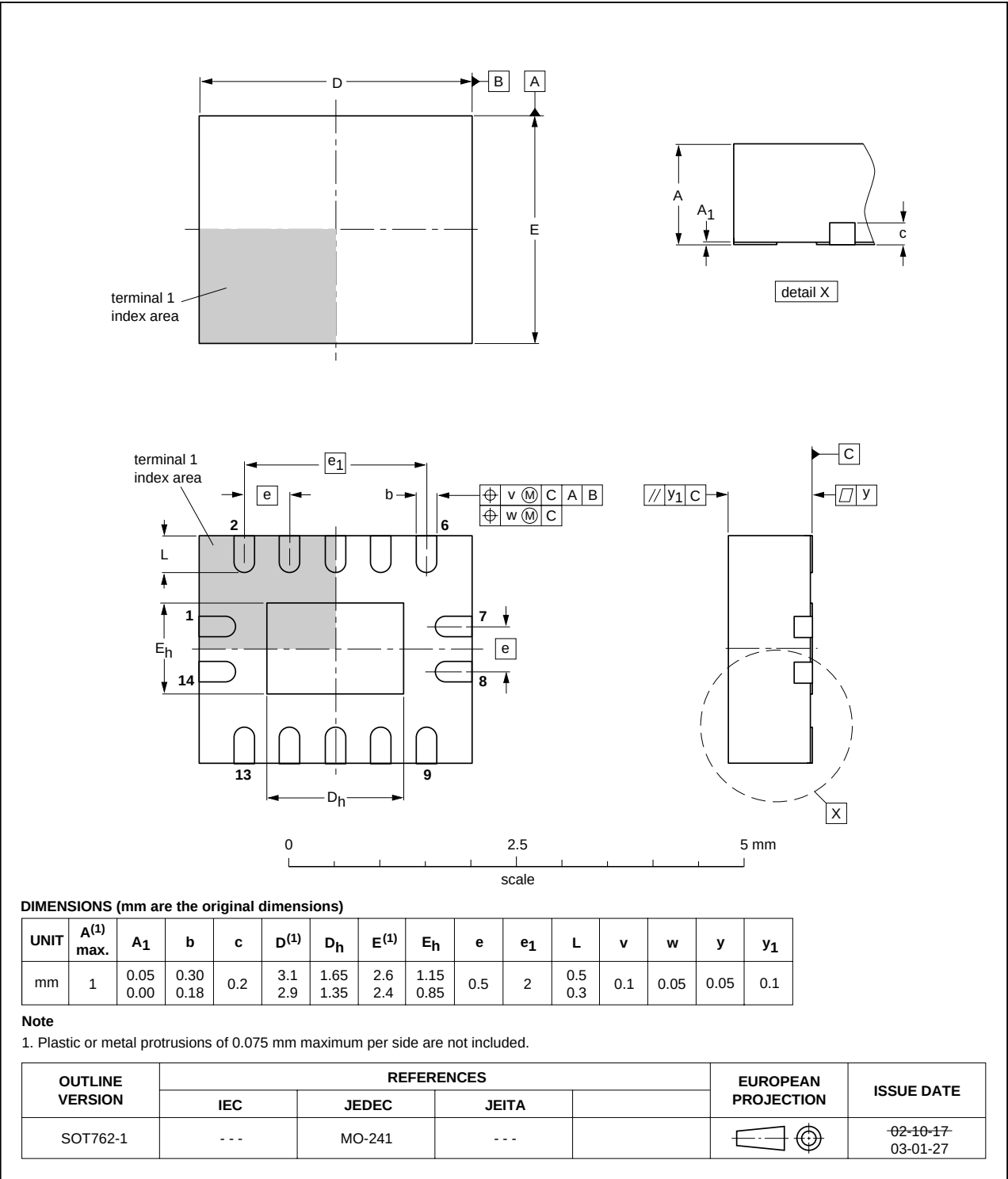


Fig 19. Package outline SOT762-1 (DHVQFN14)

17. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

18. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LV14_3	20071220	Product data sheet	-	74LV14_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 4: DHVQFN14 package added. • Section 9: derating values added for DHVQFN14 package. • Section 16: outline drawing added for DHVQFN14 package.			
74LV14_2	19980420	Product specification	-	74LV14_1
74LV14_1	19970203	Product specification	-	-

19. Legal information

19.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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